1. A process of cleaning a precision surface comprising contacting an etched precision surface having vias, cavities, trenches or channels incorporated therein with a composition which comprises liquid or supercritical carbon dioxide and a fluoride-generating species.

- 2. A process in accordance with Claim 1 wherein said fluoride-generating source is a 1 2 fluorine-containing acid.
- 3. A process in accordance with Claim 1 wherein said fluorine-containing acid is 1 selected from the group consisting of hydrogen fluoride, fluorosulfonic acid and 2 3 perfluorosulfonic acid.
- 4. A process in accordance with Claim 1 wherein said fluoride-generating species is 1 a fluorine-containing acid amine adduct. 2
- 5. A process in accordance with Claim 4 wherein said fluorine-containing amine 1 adduct is pyridine:hydrogen fluoride, amine:hydrogen fluoride or an alkylamine:hydrogen 2 3 fluoride.
- 6. A process in accordance with Claim 1 wherein said fluoride-generating species is 1 2 an amine fluoride.

ì	7. A process in accordance with Claim 1 wherein said fluoride-generating species is
2	a quaternary amine fluoride.
1	8. A process in accordance with Claim 7 wherein said quaternary amine fluoride is
2	selected from the group consisting of a tetraalkylammonium fluoride and a
3	perfluoroalkylammonium fluoride.
1	9. A process in accordance with Claim 1 wherein said fluoride-generating species is
2	a perfluororalkylsulfonyl fluoride.
1	10. A process in accordance with Claim 9 wherein said perfluororalkylsulfonyl
2	fluoride is trifluoromethylsulfonyl fluoride or perfluorooctylsulfonyl fluoride.
1	11. A process in accordance with Claim 1 wherein said fluoride-generating species is
2	an alkylsulfonylifluoride.
1	12. A process in accordance with Claim 1 wherein said fluoride-generating source is
2	an arylsulfonyl fluoride.
1	13. A process in accordance with Claim 1 wherein said fluoride-generating source is
2	an onium salt-containing fluorine.
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1	14. A process in accordance with Claim 13 wherein said onium salt containing
2	fluorine is selected from the group consisting of benzene diazonium fluoride and benzene
3	diazonium tetrafluoroborate.
1	15. A process in accordance with Claim 1 wherein said composition includes a
2	component selected from the group consisting of surfactant, a co-solvent and mixtures
3	thereof.
1	16. A process in accordance with Claim 1 wherein said contact between said
2	precision surface and said composition occurs at a pressure in the range of between about
3	1,000 psi and about 6,000 psi and at a temperature in the range of between about 40°C and
4	about 100°C.
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1	17. A process in accordance with Claim 1 wherein said precision surface is provided
2	by a semiconductor sample, a metal selected from the group consisting of aluminum, silicon,
3	tungsten, titanium, tantalium, platinum, palladium, iridium, chromium, copper and silver, a
4	polymer selected from the group consisting of polyimides and polyamides or insulators.
1	18. A process in accordance with Claim 17 wherein said precision surface is
2	provided by a semiconductor sample.
1	19. A process in accordance with Claim 18 wherein said semiconductor sample is
2	selected from the group consisting of a semiconductor wafer, a semiconductor chip, a
2	commission and a notterned film structure

1 20. A process in accordance with Claim 19 wherein said semiconductor sample is a semiconductor wafer.

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